

## 10) dimensions two in conductivity Electrical :1 Problem points)

table: following the in 9 to 0 from numbers the Write

9	8	7	6	5	4	3	2	1	0

### points) 1.2) measurements (4PP) Four-point-probe A. Part

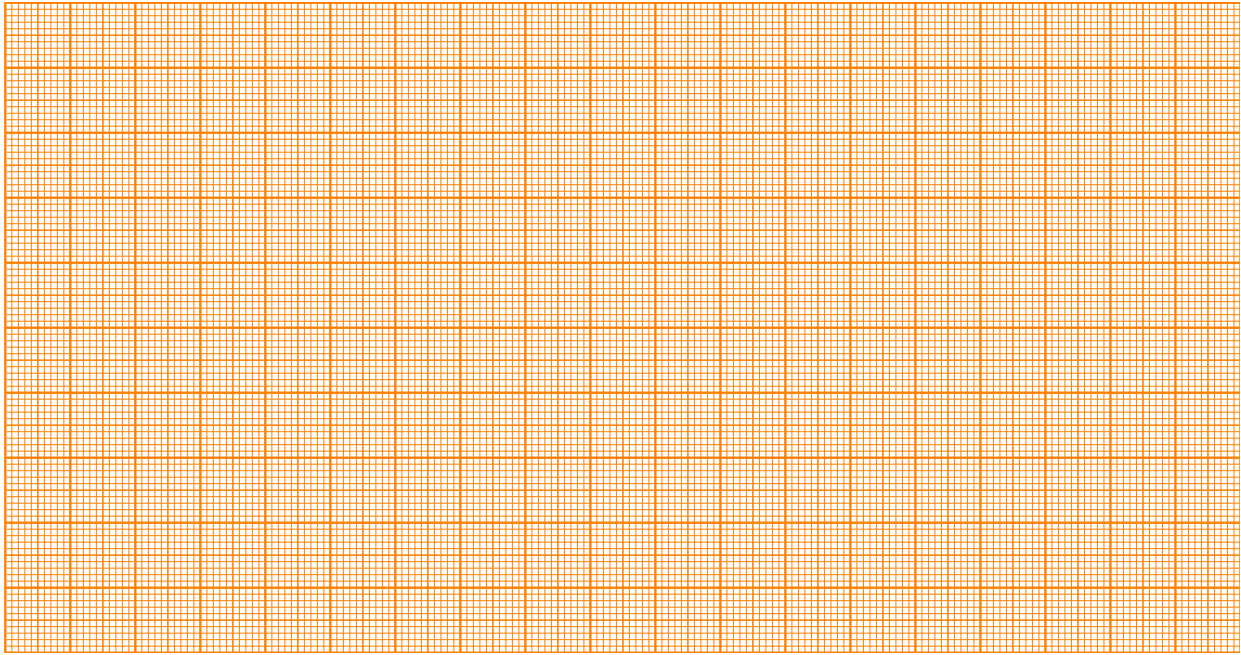
(0.6 pt) **A.1**

$s =$

$V$	$I$	$V$	$I$

**.A.1 Graph** into data your Plot

$V$  vs.  $I$  :A.1 Graph



(0.2 pt) **A.2**

$$R =$$

(0.4 pt) **A.3**

$$\Delta R =$$

points) 0.3) resistivity Sheet B. Part

(0.3 pt) **B.1**

$$\rho_{\square} \equiv \rho_{\infty} =$$

points) 3.2) dimensions sample different for Measurements C. Part

(3 pt) **C.1**

$s =$

$\rho_{\infty} =$

results. intermediate for used be can columns empty The

$\hat{R}$						(f(w/s)

(0.2 pt) **C.2**  
results. your for **C.1** Table Use

**points) 1.9) factor correction Geometrical D. Part**

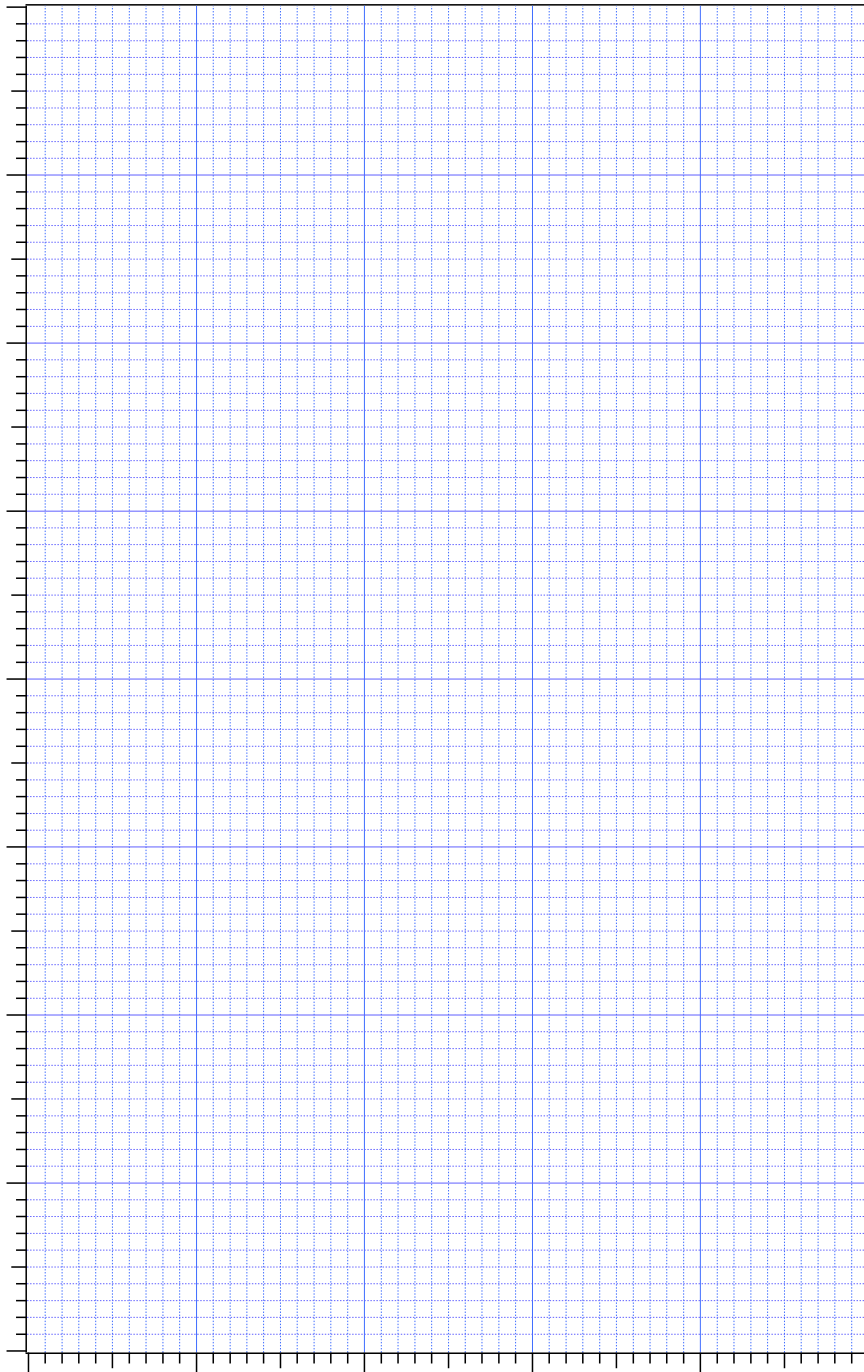
(1.0 pt) **D.1**  
double- or **(D.1b)** semi-logarithmic, **(D.1a)** (Graph linear paper: graph appropriate the on data your Plot  
pages. following the on **(D.1c)** logarithmic

(0.9 pt) **D.2**

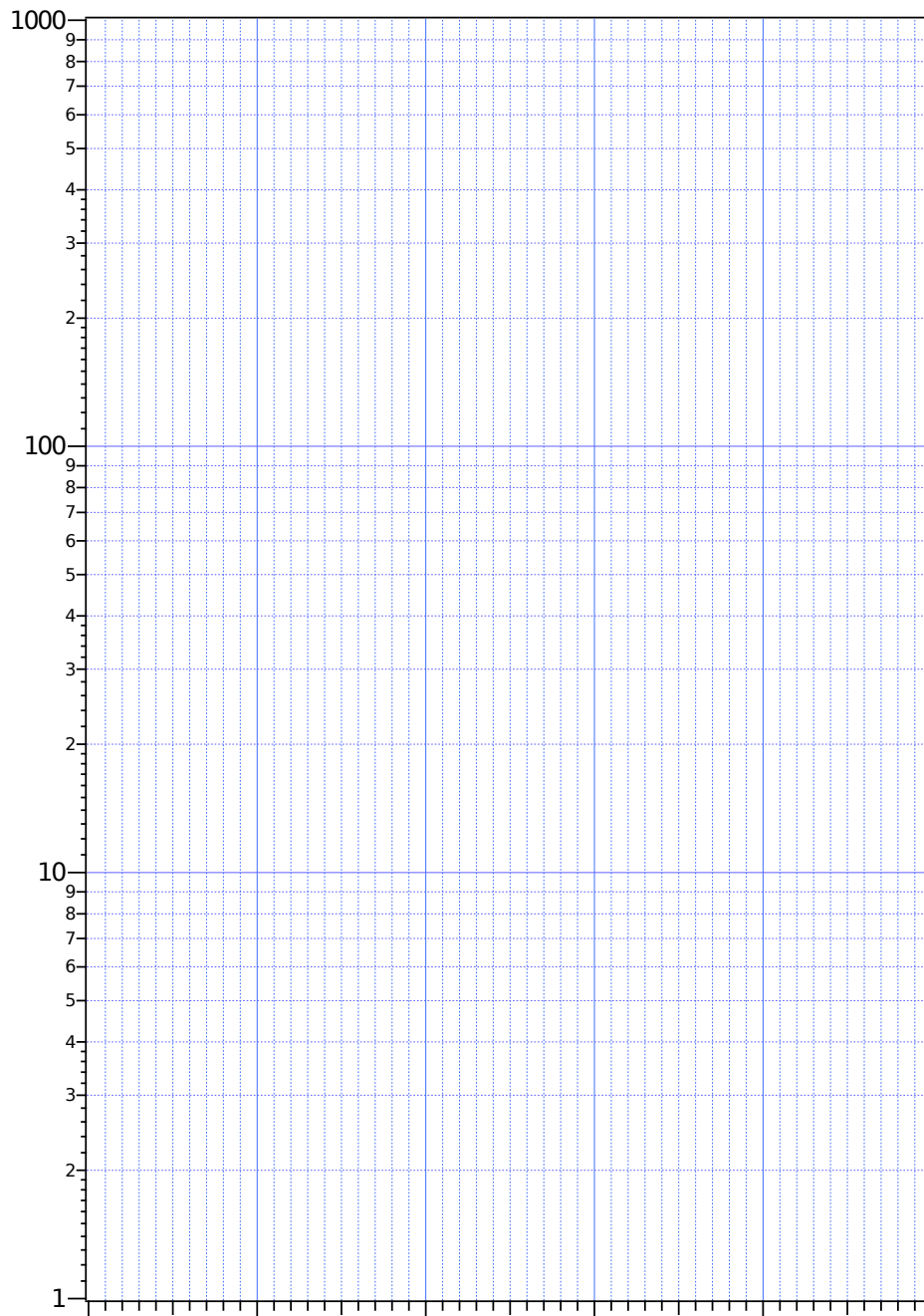
$a =$

$b =$

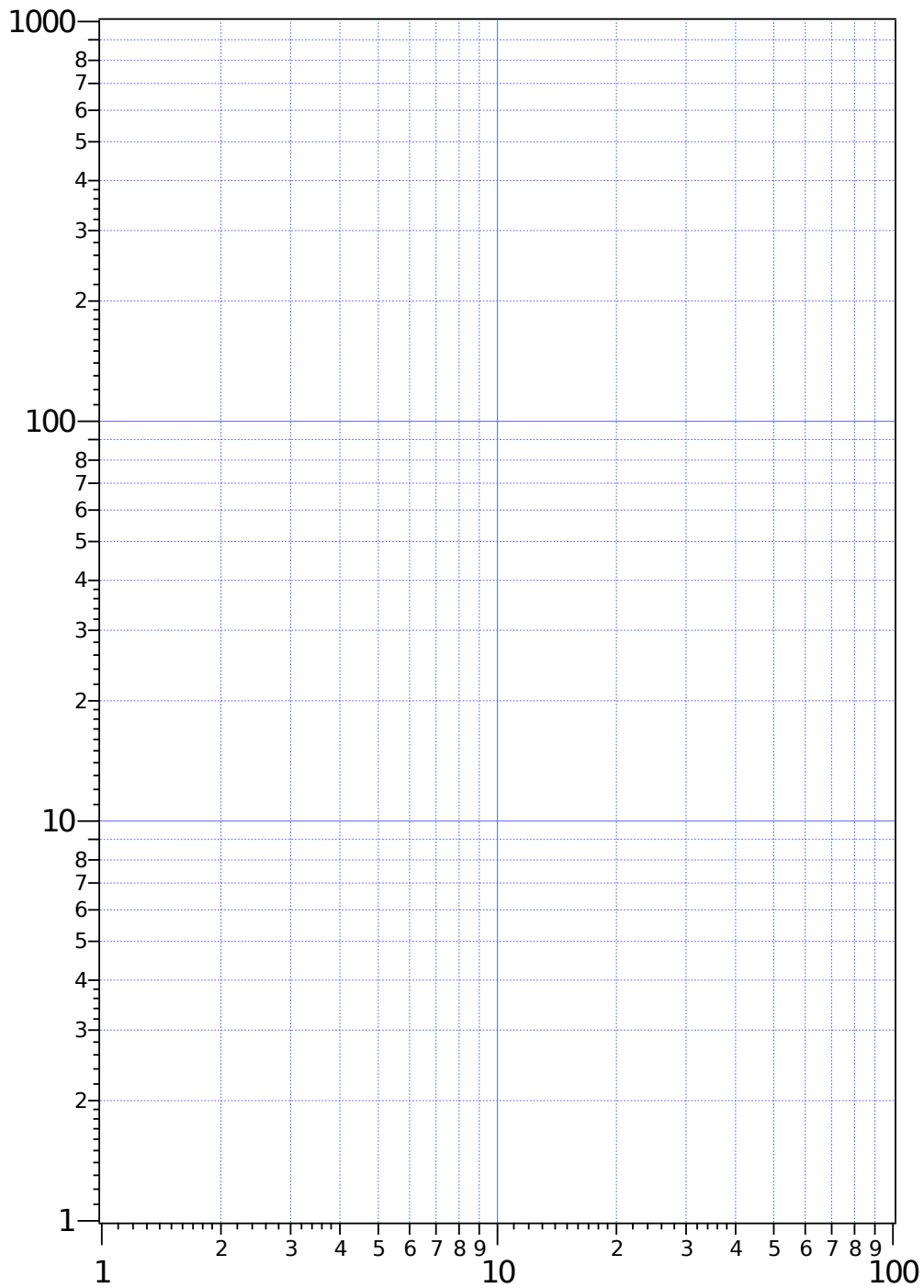
scale: linear D.1a: Graph



scale: semi-log D.1b: Graph



scale: double-log D1c: Graph



**points) 3.4) Pauw-method der van the and wafer silicon The E. Part**

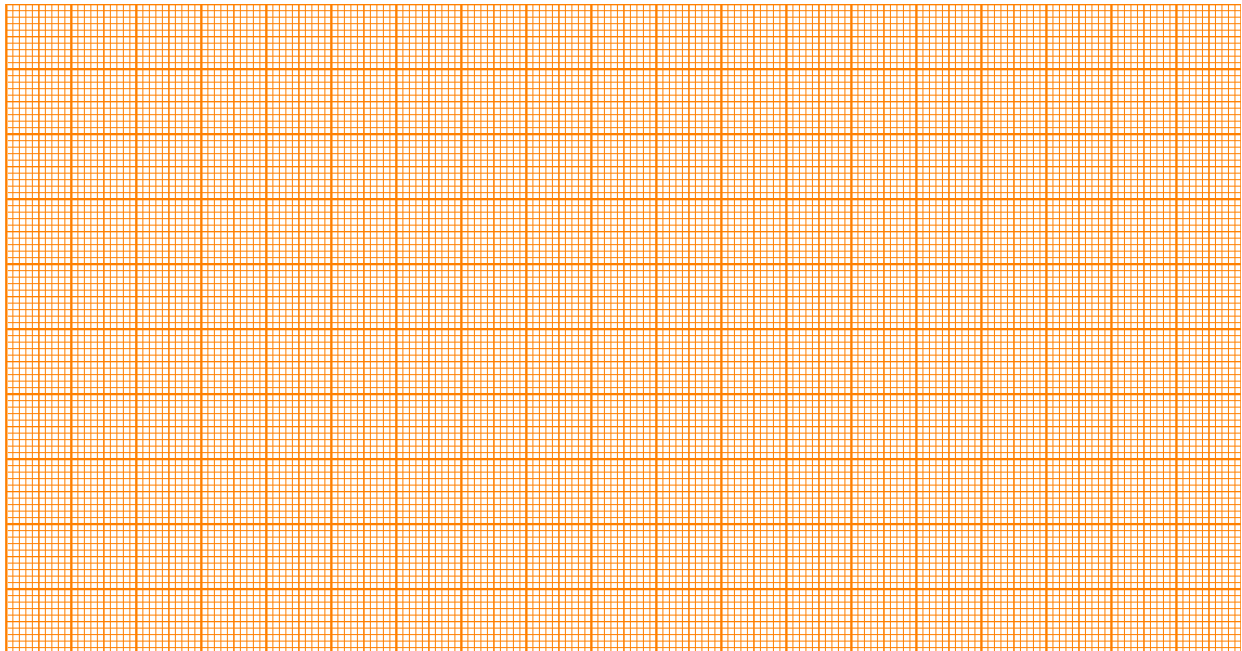
here: wafer your of number the Note

(0.4 pt) **E.1**

$V$	$I$	$V$	$I$

(0.4 pt) **E.2**

**$V$  vs  $I$  :E.2 Graph**



$R_{4PP} =$



(0.2 pt) **E.3**

$f(w/s) =$

$w =$   $\rightarrow w/s =$

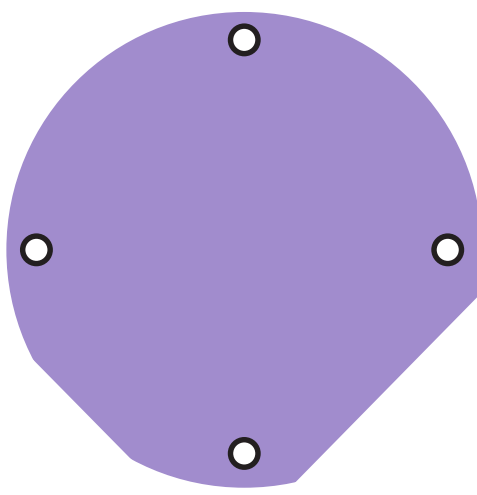
(0.1 pt) **E.4**

$\rho_{\square}(4PP)$

(0.6 pt) **E.5**

$V$	$I$

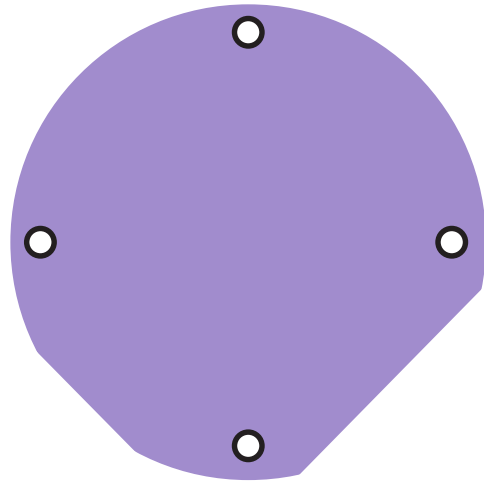
current): the of (orientation Sketch



(0.6 pt) **E.6**

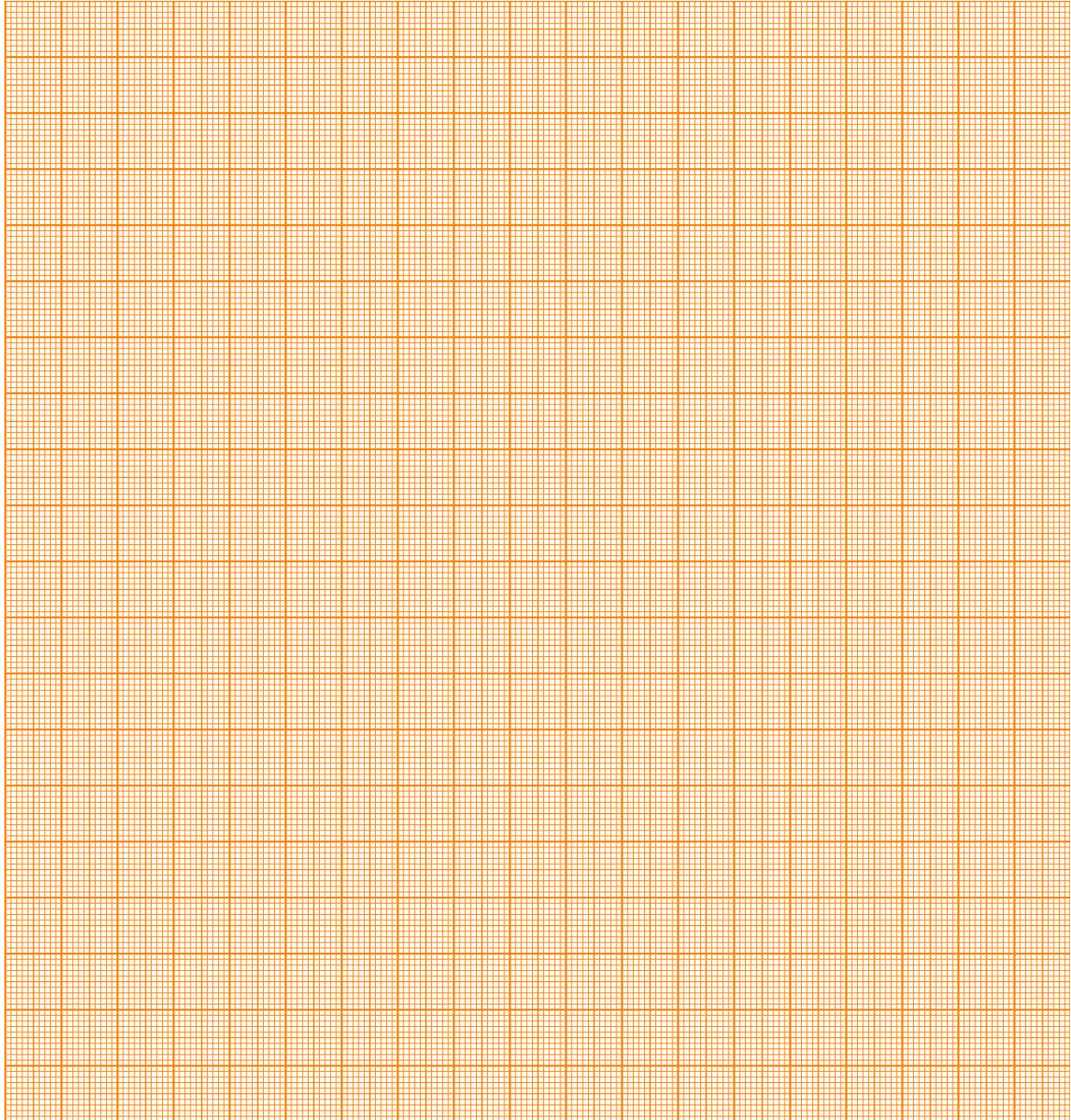
$V$	$I$

current): the of (orientation Sketch



(0.5 pt) **E.7**

*V* vs. *I* : **E.7 Graph**



$\langle R \rangle =$

(0.4 pt) **E.8**  
Calculation:

$$\rho_{\square}(\text{vdP}) =$$

(0.1 pt) **E.9**

$$\frac{\Delta \rho_{\square}}{\rho_{\square}(\text{vdP})} = \quad = \quad \%$$

(0.1 pt) **E.10**

$\rho$  = film thin Cr the of Resistivity